

ZXTP19020DFF

20V, SOT23F, PNP medium power transistor

Summary

$BV_{CEO} > -20V$

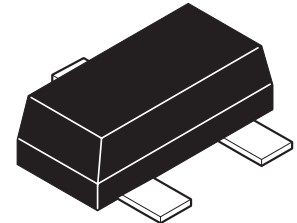
$BV_{ECO} > -4V$

$I_{C(cont)} = 5.5A$

$V_{CE(sat)} < 44mV @ 1A$

$R_{CE(sat)} = 26m\Omega$

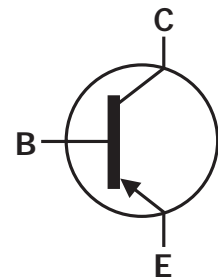
$P_D = 1.5W$



Complementary part number: ZXTN19020DFF

Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium



Features

- High power dissipation SOT23 package
- 15A peak current
- Guaranteed gain at a collector current of 10A
- Very low saturation voltage

Applications

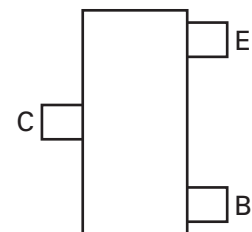
- MOSFET and IGBT gate driving
- Power switches
- Motor control

Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP19020DFFTA	7	8	3000

Device marking

1D8



Pinout - top view

ZXTP19020DFF

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	-25	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	-4	V
Emitter-base voltage	V_{EBO}	-7	V
Continuous collector current ^(c)	I_C	-5.5	A
Peak pulse current	I_{CM}	-15	A
Base current	I_B	-1	A
Power dissipation at $T_{amb} = 25^{\circ}\text{C}^{(a)}$	P_D	0.84	W
Linear derating factor		6.72	mW/ $^{\circ}\text{C}$
Power dissipation at $T_{amb} = 25^{\circ}\text{C}^{(b)}$	P_D	1.34	W
Linear derating factor		10.72	mW/ $^{\circ}\text{C}$
Power dissipation at $T_{amb} = 25^{\circ}\text{C}^{(c)}$	P_D	1.5	W
Linear derating factor		12	mW/ $^{\circ}\text{C}$
Power dissipation at $T_{amb} = 25^{\circ}\text{C}^{(d)}$	P_D	2	W
linear derating factor		16	mW/ $^{\circ}\text{C}$
Operating and storage temperature range	T_J, T_{stg}	-55 to 150	$^{\circ}\text{C}$

Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	149.3	$^{\circ}\text{C/W}$
Junction to ambient ^(b)	$R_{\theta JA}$	93.4	$^{\circ}\text{C/W}$
Junction to ambient ^(c)	$R_{\theta JA}$	83.3	$^{\circ}\text{C/W}$
Junction to ambient ^(d)	$R_{\theta JA}$	60	$^{\circ}\text{C/W}$
Junction to case ^(e)	$R_{\theta JC}$	38	$^{\circ}\text{C/W}$

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

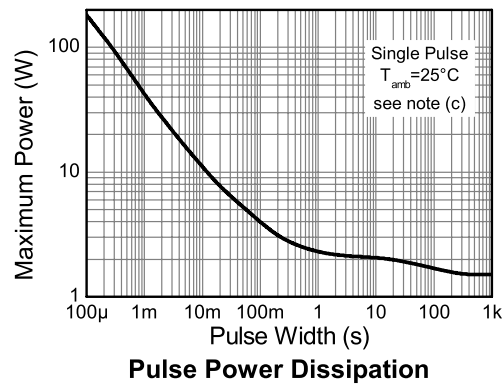
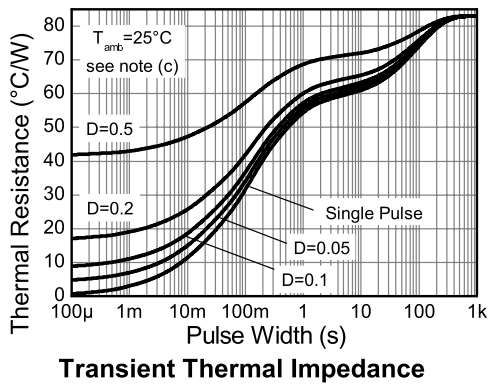
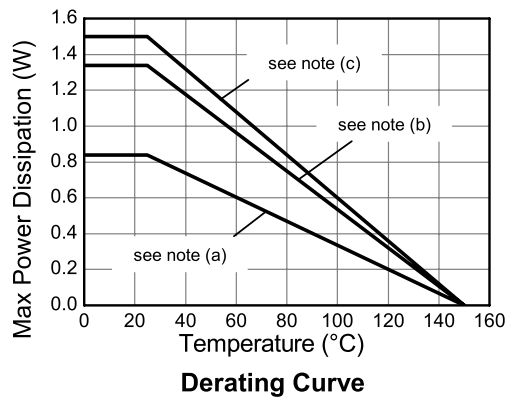
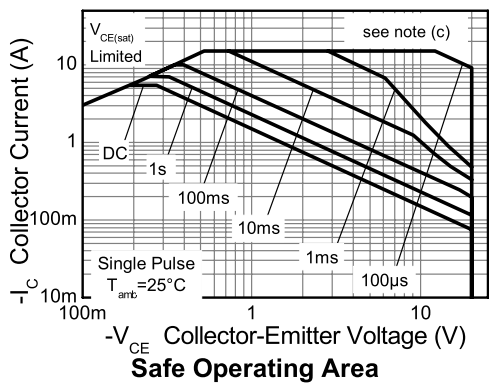
(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5\text{secs}$

(e) Junction to case from collector tab

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Characteristics



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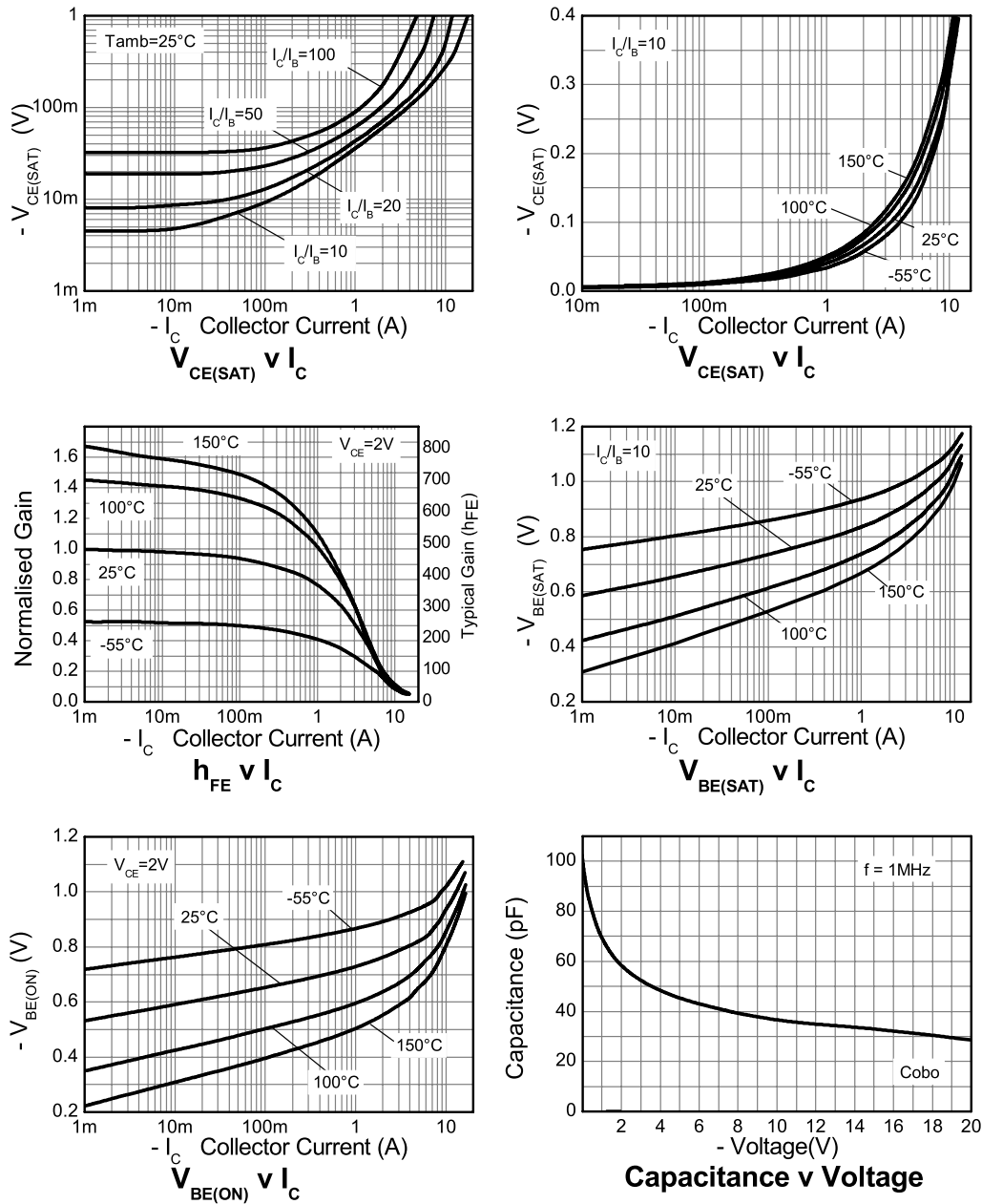
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-25	-55		V	$I_C = -100\mu\text{A}$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	-20	-50		V	$I_C = -10\text{mA}^{(*)}$
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	-4	-8.6		V	$I_E = -100\mu\text{A}$, $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-collector breakdown voltage (base open)	BV_{ECO}	-4	-8.6		V	$I_E = -100\mu\text{A}$
Emitter-base breakdown voltage	BV_{EBO}	-7	-8.2		V	$I_E = -100\mu\text{A}$
Collector-base cut-off current	I_{CBO}		<-1	-50 -0.5	nA μA	$V_{CB} = -25\text{V}$ $V_{CB} = -25\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Emitter-base cut-off current	I_{EBO}		<-1	-50	nA	$V_{EB} = -5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		-37	-44	mV	$I_C = -1\text{A}$, $I_B = -100\text{mA}^{(*)}$
			-90	-125	mV	$I_C = -1\text{A}$, $I_B = -10\text{mA}^{(*)}$
			-105	-140	mV	$I_C = -2\text{A}$, $I_B = -40\text{mA}^{(*)}$
			-160	-210	mV	$I_C = -5\text{A}$, $I_B = -250\text{mA}^{(*)}$
			-145	-175	mV	$I_C = -5.5\text{A}$, $I_B = -550\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		-975	-1050	mV	$I_C = -5.5\text{A}$, $I_B = -550\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		-830	-900	mV	$I_C = -5.5\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
Static forward current transfer ratio	h_{FE}	300	450	900		$I_C = -100\text{mA}$, $V_{CE} = -2\text{V}^{(*)}$
		200	310			$I_C = -2\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
		85	130			$I_C = -5.5\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
		25	50			$I_C = -10\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
			20			$I_C = -15\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
Transition frequency	f_T		176		MHz	$I_C = -50\text{mA}$, $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Input capacitance	C_{ibo}			400	pF	$V_{EB} = -0.5\text{V}$, $f = 1\text{MHz}^{(*)}$
Output capacitance	C_{obo}		36	45	pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}^{(*)}$
Delay time	t_d		23		ns	$I_C = -1\text{A}$, $V_{CC} = -10\text{V}$ $I_{B1} = -I_{B2} = -50\text{mA}$.
Rise time	t_r		18.4		ns	
Storage time	t_s		266		ns	
Fall time	t_f		49.6		ns	

NOTES:

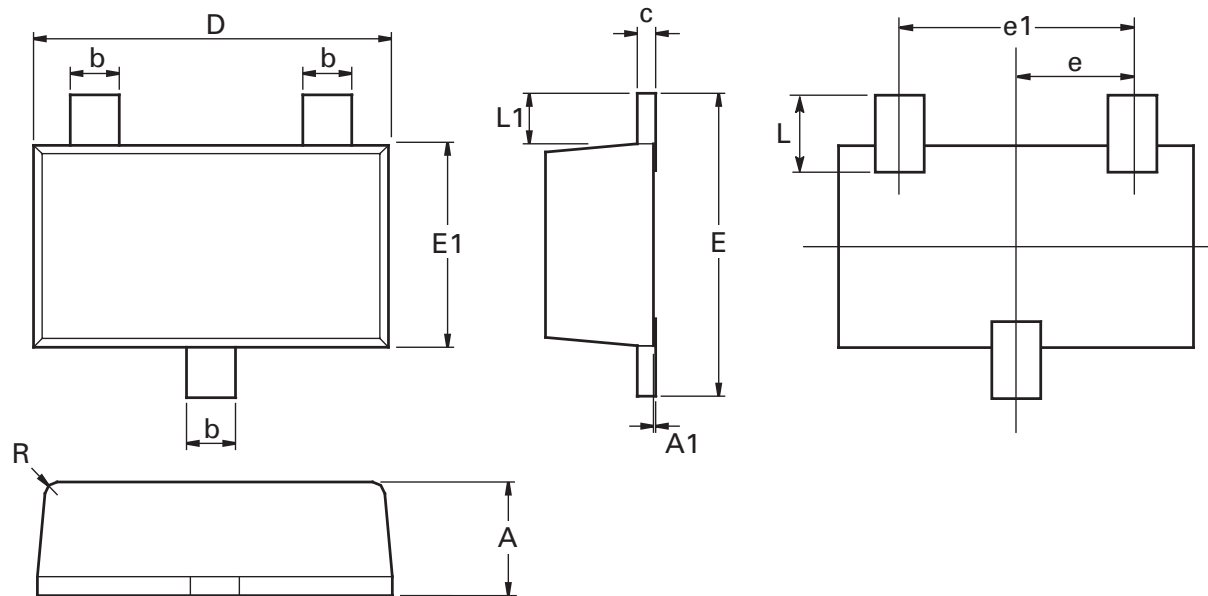
(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



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SOT23F Package outline



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.80	1.00	0.0315	0.0394	E	2.30	2.50	0.0906	0.0984
A1	0.00	0.10	0.00	0.0043	E1	1.50	1.70	0.0590	0.0669
b	0.35	0.45	0.0153	0.0161	L	0.48	0.68	0.0189	0.0268
c	0.10	0.20	0.0043	0.0079	L1	0.30	0.50	0.0153	0.0161
D	2.80	3.00	0.1102	0.1181	R	0.05	0.15	0.0019	0.0059
e	0.95 ref		0.0374 ref		O	0°	12°	0°	12°
e1	1.80	2.00	0.0709	0.0787	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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Zetex sales offices

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Kustermann-park Balanstraße 59 D-81541 München Germany Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Zetex Inc 700 Veterans Memorial Highway Hauppauge, NY 11788 USA Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Zetex (Asia Ltd) 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

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